

# MOSFET – N-Channel, QFET

100 V, 15.6 A, 100 mΩ

## FQD19N10L

### Description

This N-Channel enhancement mode power MOSFET is produced using onsemi's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

### Features

- 15.6 A, 100 V,  $R_{DS(on)}$  = 100 mΩ (Max.) @  $V_{GS}$  = 10 V
- Low Gate Charge (Typ. 14 nC)
- Low  $C_{rss}$  (Typ. 35 pF)
- 100% Avalanche Tested

### ABSOLUTE MAXIMUM RATINGS ( $T_C$ = 25°C, unless otherwise noted)

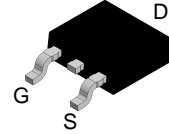
Symbol	Parameter	Ratings	Unit
$V_{DSS}$	Drain-Source Voltage	100	V
$I_D$	Drain Current	- Continuous ( $T_C$ = 25°C)	15.6 A
		- Continuous ( $T_C$ = 100°C)	9.8 A
$I_{DM}$	Drain Current	- Pulsed (Note 1)	62.4 A
$V_{GSS}$	Gate-Source Voltage	±20	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	220	mJ
$I_{AR}$	Avalanche Current (Note 1)	15.6	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	5.0	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	6.0	V/ns
$P_D$	Power Dissipation ( $T_A$ = 25°C) *	2.5	W
	Power Dissipation ( $T_C$ = 25°C) - Derate Above 25°C	50 0.4	W W/°C
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	°C
$T_L$	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

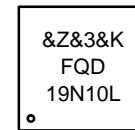
Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance Junction to Case, Max.	2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	
	Thermal Resistance, Junction to Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max.	50	

$V_{DSS}$	$R_{DS(on)}$ MAX	$I_D$ MAX
100 V	100 mΩ @ 10 V	15.6 A

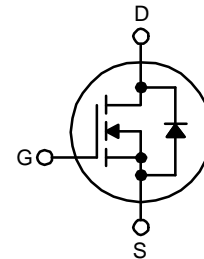


DPAK3 (TO-252 3 LD)  
CASE 369AS

### MARKING DIAGRAM



- &Z = Assembly Plant Code
- &3 = 3-Digit Date Code
- &K = 2-Digits Lot Run Traceability Code
- FQD19N10L = Device Code



N-Channel MOSFET

### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

# FQD19N10L

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

BV <sub>DSS</sub>	Drain–Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	100	–	–	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C	–	0.09	–	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V	–	–	1	μA
		V <sub>DS</sub> = 80 V, T <sub>C</sub> = 125°C	–	–	10	μA
I <sub>GSSF</sub>	Gate–Body Leakage Current, Forward	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0 V	–	–	100	nA
I <sub>GSSR</sub>	Gate–Body Leakage Current, Reverse	V <sub>GS</sub> = –20 V, V <sub>DS</sub> = 0 V	–	–	–100	nA

### ON CHARACTERISTICS

V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.0	–	2.0	V
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7.8 A	–	0.074	0.10	Ω
		V <sub>GS</sub> = 5 V, I <sub>D</sub> = 7.8 A	–	0.082	0.11	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 30 V, I <sub>D</sub> = 7.8 A	–	14	–	S

### DYNAMIC CHARACTERISTICS

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz	–	670	870	pF
C <sub>oss</sub>	Output Capacitance		–	160	210	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		–	35	45	pF

### SWITCHING CHARACTERISTICS

t <sub>d(on)</sub>	Turn–On Delay Time	V <sub>DD</sub> = 50 V, I <sub>D</sub> = 19 A, R <sub>G</sub> = 25 Ω (Note 4)	–	14	38	ns
t <sub>r</sub>	Turn–On Rise Time		–	410	830	ns
t <sub>d(off)</sub>	Turn–Off Delay Time		–	20	50	ns
t <sub>f</sub>	Turn–Off Fall Time		–	140	290	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 80 V, I <sub>D</sub> = 19 A, V <sub>GS</sub> = 5 V (Note 4)	–	14	18	nC
Q <sub>gs</sub>	Gate–Source Charge		–	2.9	–	nC
Q <sub>gd</sub>	Gate–Drain Charge		–	9.2	–	nC

### DRAIN–SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

I <sub>S</sub>	Maximum Continuous Drain–Source Diode Forward Current	–	–	15.6	A	
I <sub>SM</sub>	Maximum Pulsed Drain–Source Diode Forward Current	–	–	62.4	A	
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 15.6 A	–	–	1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 19 A, di <sub>F</sub> / dt = 100 A/μs	–	80	–	ns
Q <sub>rr</sub>	Reverse Recovery Charge		–	0.195	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Repetitive rating: pulse–width limited by maximum junction temperature.
2. L = 1.35 mH, I<sub>AS</sub> = 15.6 A, V<sub>DD</sub> = 25 V, R<sub>G</sub> = 25 Ω, starting T<sub>J</sub> = 25°C.
3. I<sub>SD</sub> ≤ 19 A, di/dt ≤ 300 A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C.
4. Essentially independent of operating temperature.

# FQD19N10L

## TYPICAL CHARACTERISTICS

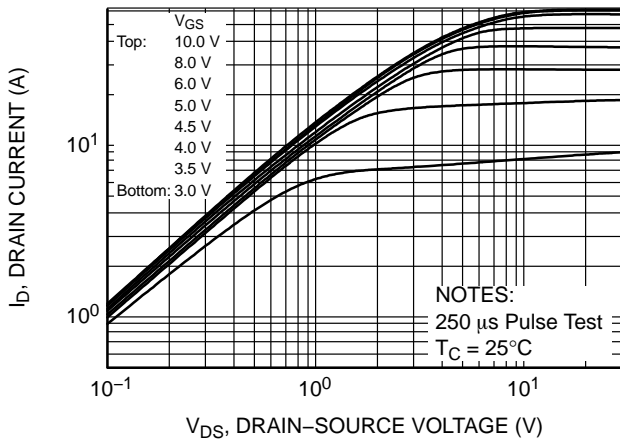


Figure 1. On-Region Characteristics

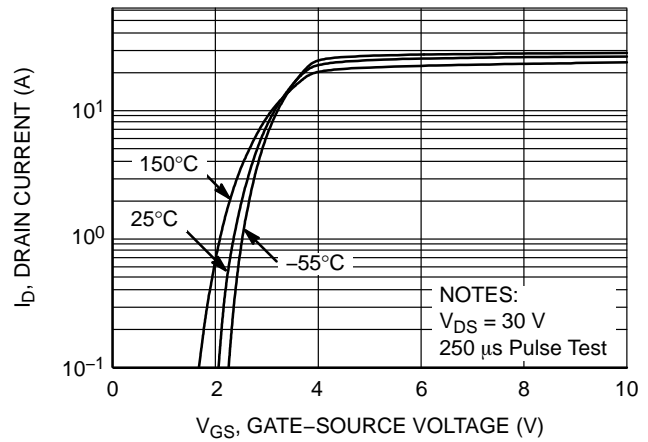


Figure 2. Transfer Characteristics

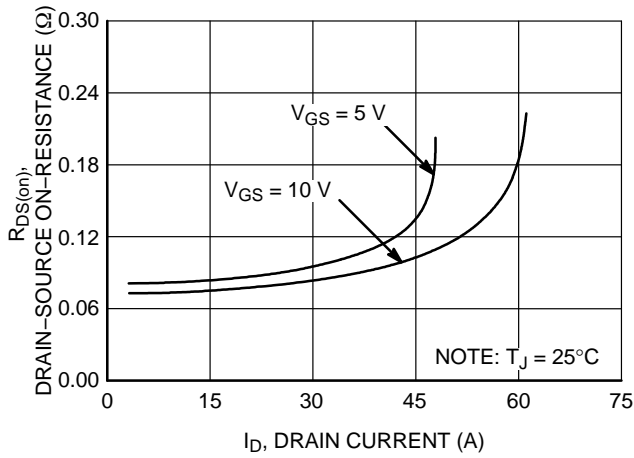


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

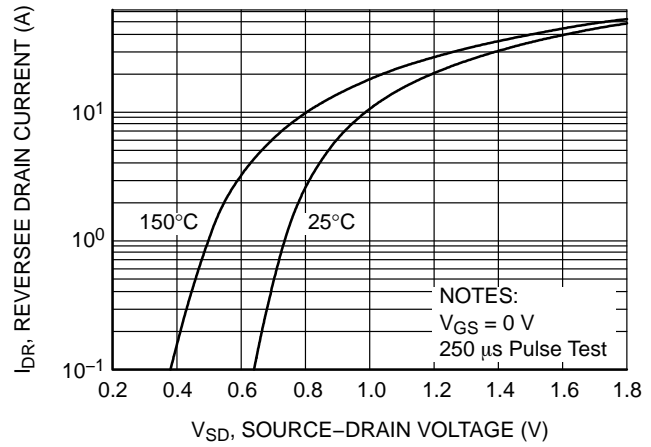


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

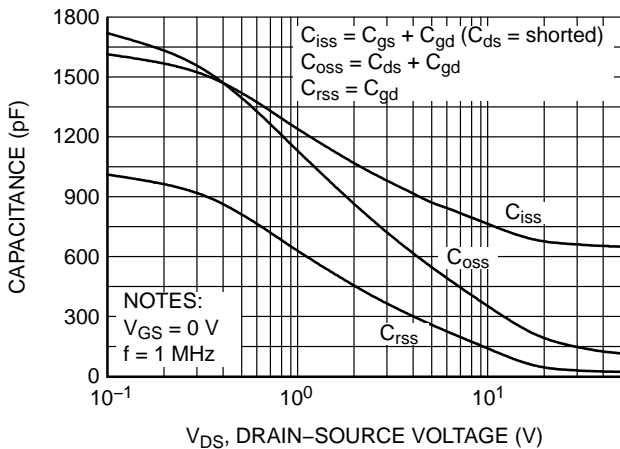


Figure 5. Capacitance Characteristics

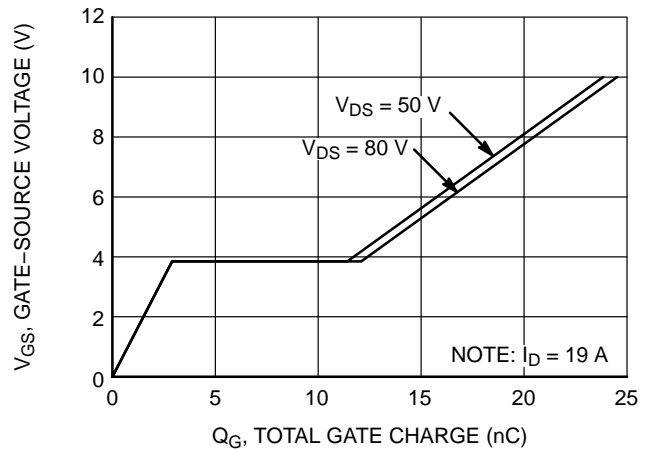
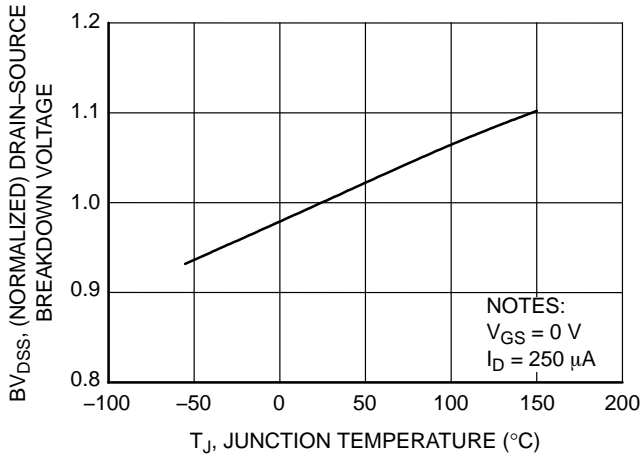


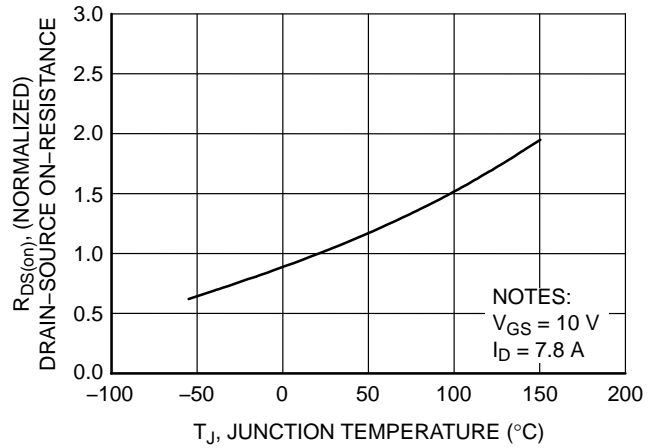
Figure 6. Gate Charge Characteristics

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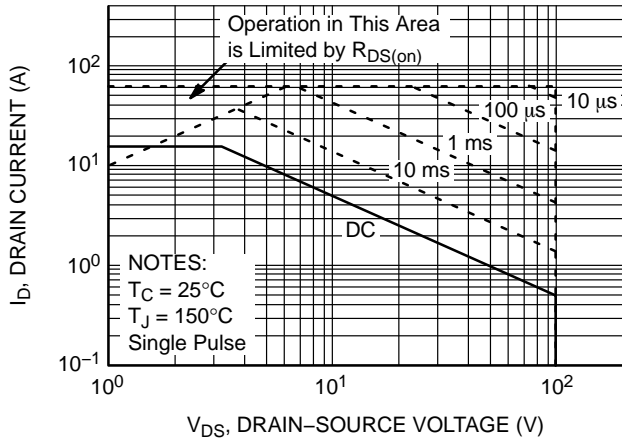
## TYPICAL CHARACTERISTICS (continued)



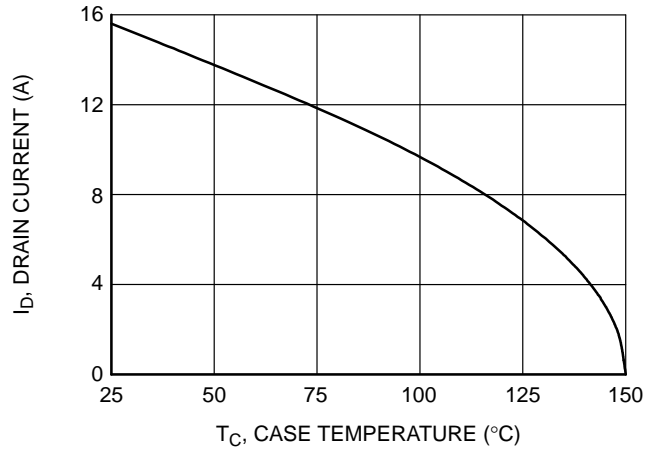
**Figure 7. Breakdown Voltage Variation vs. Temperature**



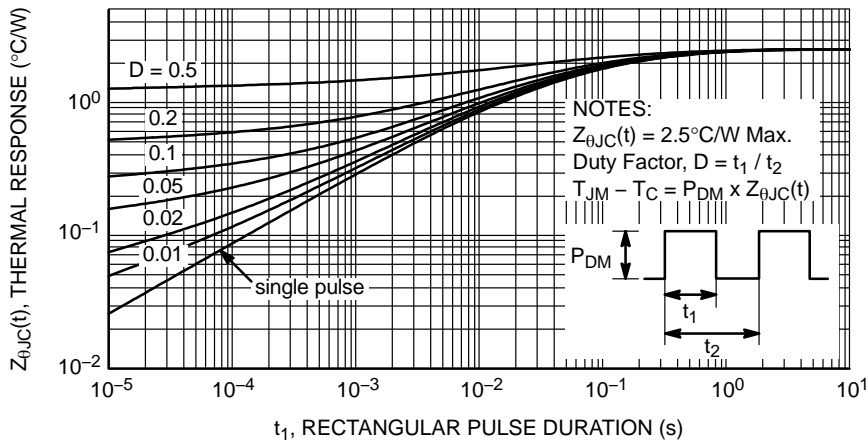
**Figure 8. On-Resistance Variation vs. Temperature**



**Figure 9. Maximum Safe Operating Area**



**Figure 10. Maximum Drain Current vs. Case Temperature**



**Figure 11. Transient Thermal Response Curve**

# FQD19N10L

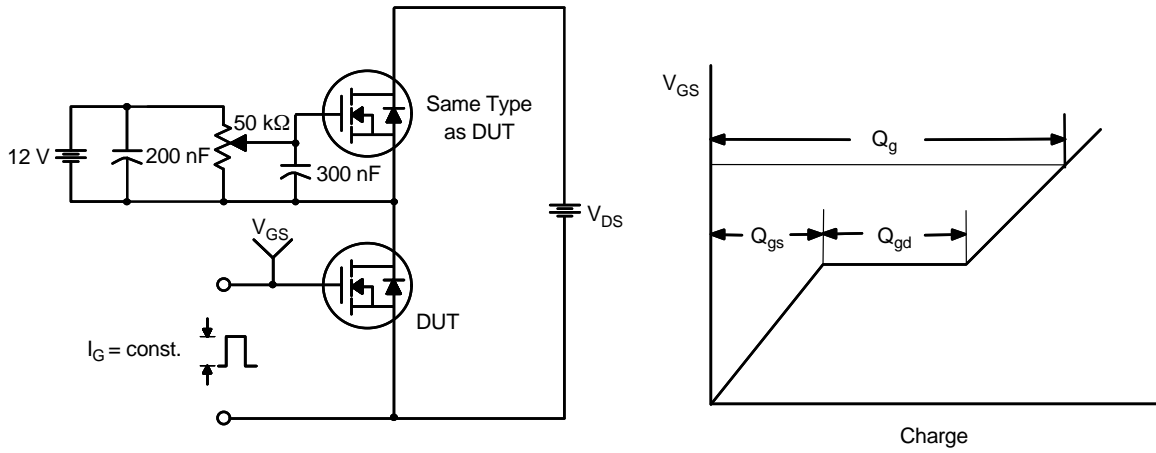


Figure 12. Gate Charge Test Circuit & Waveform

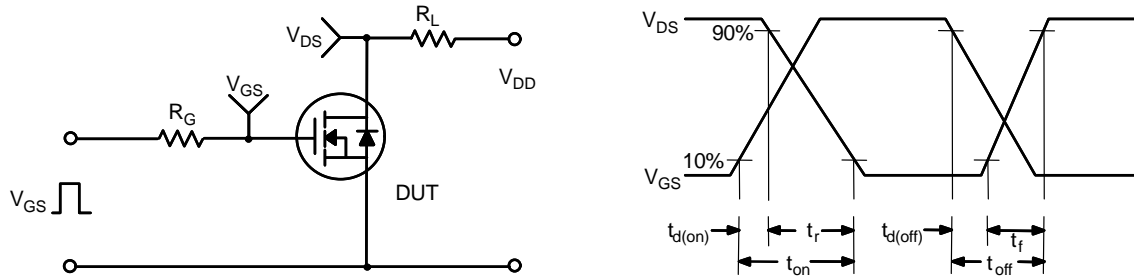


Figure 13. Resistive Switching Test Circuit & Waveforms

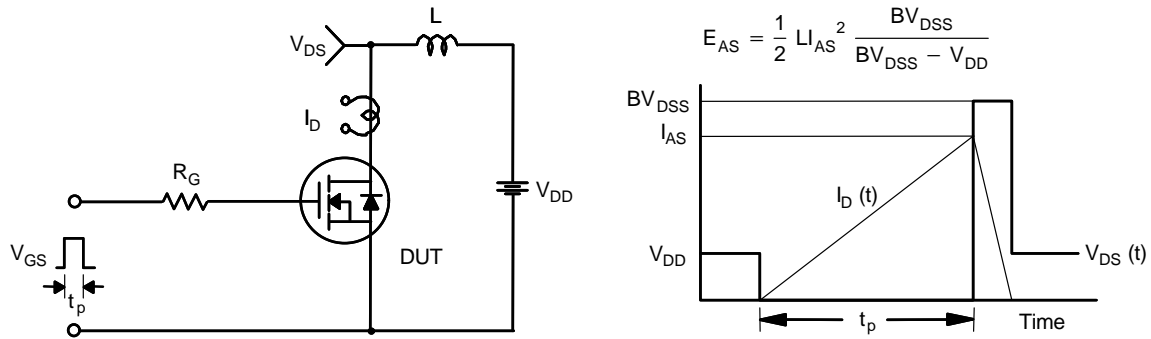
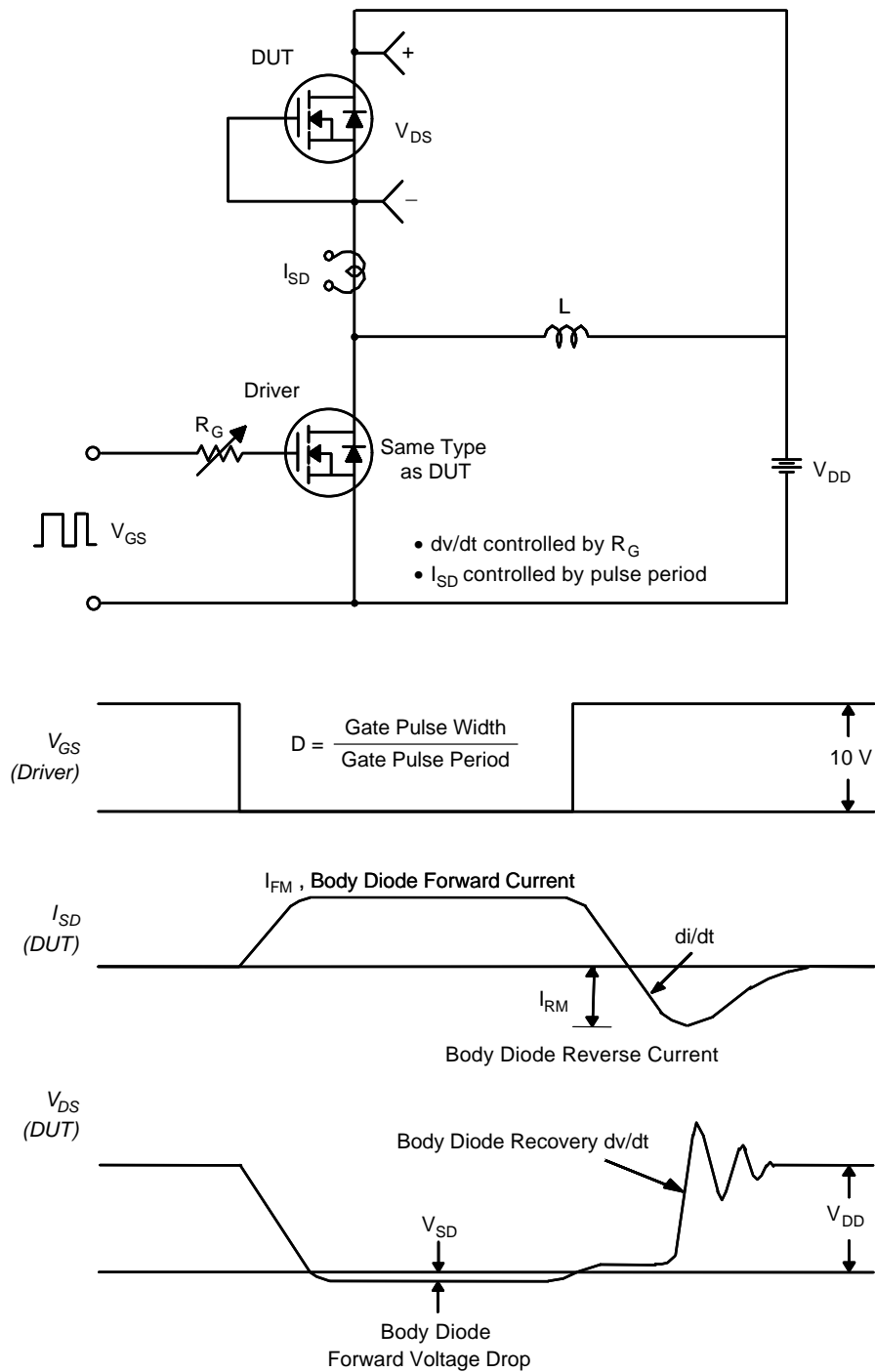


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

## FQD19N10L



**Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms**

### PACKAGE MARKING AND ORDERING INFORMATION

Device	Device Marking	Package	Reel Size	Tape Width	Shipping†
FQD19N10LTM	FQD19N10L	DPAK3 (TO-252 3 LD)	330 mm	16 mm	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

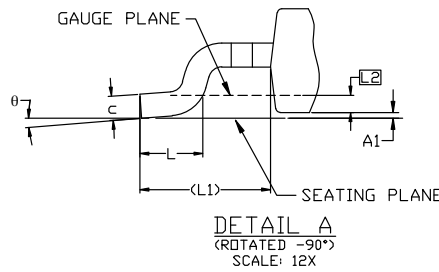


## DPAK3 6.10x6.54x2.29, 4.57P CASE 369AS ISSUE B

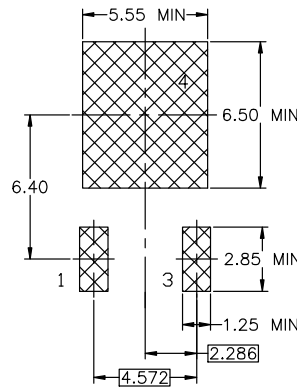
DATE 20 DEC 2023



- NOTES: UNLESS OTHERWISE SPECIFIED
- A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE F, VARIATION AA.
  - B) ALL DIMENSIONS ARE IN MILLIMETERS.
  - C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2018.
  - D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
  - E) FOR DIODE PRODUCTS, L4 IS 0.25 MM MAX PLASTIC BODY STUB WITHOUT CENTER LEAD.
  - F) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
  - G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TD228P991X239-3N.



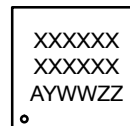
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	2.18	2.29	2.39
A1	0.00	-	0.127
b	0.64	0.77	0.89
b2	0.76	0.95	1.14
b3	5.21	5.34	5.46
c	0.45	0.53	0.61
c2	0.45	0.52	0.58
D	5.97	6.10	6.22
D1	5.21	---	---
E	6.35	6.54	6.73
E1	4.32	---	---
e	2.286 BSC		
e1	4.572 BSC		
H	9.40	9.91	10.41
L	1.40	1.59	1.78
L1	2.90 REF		
L2	0.51 BSC		
L3	0.89	1.08	1.27
L4	---	---	1.02
theta	0°	---	10°



### LAND PATTERN RECOMMENDATION

\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

### GENERIC MARKING DIAGRAM\*



\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

XXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
ZZ = Assembly Lot Code

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<b>DESCRIPTION:</b>	<b>DPAK3 6.10x6.54x2.29, 4.57P</b>	<b>PAGE 1 OF 1</b>

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